

Reactive magnetron sputtering model at making Ti-TiO_x coatings

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Abstract

© Published under licence by IOP Publishing Ltd. Mathematical model of reactive magnetron sputtering for plant VU 700-D is described. Approximating curves for experimental current-voltage characteristic for two gas input schemas are shown. Choice of gas input schema influences on model parameters (mainly on pumping speed). Reactive magnetron sputtering model allows develop technology of Ti - TiO_x coatings deposition without changing atmosphere and pressure in vacuum chamber.

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